

Please amend the application as follows:

In the Specification

Please delete the paragraph at page 49, line 5.

Please replace the paragraph at page 24, lines 3 through 10 with the following paragraph:

a-1 Referring to FIG. 5C, a Boron Phosphorus Silica Glass (BPSG) 134 of SiO_2 is formed over the circuit. A portion is etched away and an aluminum terminal 136 is added. Referring to FIG. 5D, a layer of Phosphorus Silica Glass (PSG) 138 of SiO_2 is formed over the BPSG 134 and the aluminum terminal 136. A titanium (Ti) black matrix 140 is located over the transistor as a light shield. A silica passivation 142 is formed over the entire wafer. The wafer is ready for the next assembly process.

Please replace the paragraph at page 50, lines 1 through 7 with the following paragraph:

a2 It is recognized that modulating V_{COM} or initializing can be done individually or in combination. It is desired to drive black first with LVV, also referred to as modulating V_{COM} , and set white with initialization. The combination allows for lower voltages and takes advantage of the fact that the response time driving white to black is quicker than the response time driving black to white.

Amendments to the specification are indicated in the attached "Marked Up Version of Amendments" (page i).

In the Claims

Please amend Claim 12. Amendments to the claims are indicated in the attached "Marked Up Version of Amendments" (page i).